

IEEE EDS Mini-colloquium on Nanometer CMOS Technology: (WIMNACT 26)

Sponsored by IEEE EDS Japan Chapter

Co-sponsored by Global COE Photonics Integration-Core Electronics (PICE), Tokyo Institute of Technology, Tokyo Institute of Technology

Co-sponsored by Frontier Research Center

Organization:

General Chair: Shin-ichiro Kimura, Chair, IEEE EDS Japan Chapter

Program Chair: Hiroshi Iwai, Tokyo Institute of Technology

Publicity Chair: Kazuo Tsutsui, Tokyo Institute of Technology

Publication Chair: Kuniyuki Kakushima, Tokyo Institute of Technology

Local Arrangement Chair, Parhat Ahmet, Tokyo Institute of Technology

Place: Meeting room, 2<sup>nd</sup> floor, Frontier Research Center, Tokyo Institute of Technology, Yokohama, Japan

Date: February 9, 2011

12:20-12:25 Opening

12:25-12:35 Introduction of IEEE EDS,

Sinichiro Kimura, Chair, EDS Japan Chapter

12:35-12:50 Introductory talk, Future of Nano CMOS Technology:

Hiroshi Iwai, Tokyo Institute of Technology

12:50-13:35 The future of Nanoelectronics by Scaling of CMOS and Functional Diversification:

Simon Delelonibus, Leti

13:35-14:20 SOI opportunities to speed up, save energy and memorize:

Sorin Cristoloveanu, IMEP, Grenoble Polytechnic Institute

14:20-15:05 The Case for Modeling and Simulation:

Claudio Fiegna, University of Bologna

15:05-15:30 Coffee Break

15:30-16:15 Advanced simulation of nanotransistors:

Francisco Gamiz, University of Granada

16:15-17:00 Methods for Improving Electrical Properties of La<sub>2</sub>O<sub>3</sub>-based Gate Dielectric Films:

Hei Wong, City University of Hong Kong

17:00-17:45 Memory Effects in SOI-FinFET with ONO Buried Insulator:

Jong-Hyun Lee, Kyungpook National University

17:45-18:00 Closing Talk, Nano-Electronic Devices based on Silicon MOS Structure:

Chandan Sarkar, Jadavpur University